

## R-C Thermal Model Parameters

### DESCRIPTION

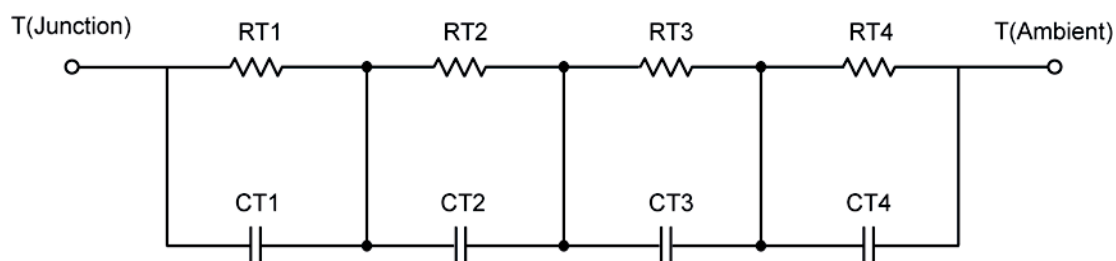
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



| <b>R-C VALUES FOR TANK CONFIGURATION</b> |            |            |      |
|------------------------------------------|------------|------------|------|
| Thermal Resistance (°C/W)                |            |            |      |
| Junction to                              | Ambient    | Case       | Foot |
| RT1                                      | 7.9269     | 469.8537 m | N/A  |
| RT2                                      | 1.8924     | 248.1578 m | N/A  |
| RT3                                      | 11.4965    | 477.8885 m | N/A  |
| RT4                                      | 43.6842    | 1.4041     | N/A  |
| Thermal Capacitance (Joules/°C)          |            |            |      |
| Junction to                              | Ambient    | Case       | Foot |
| CT1                                      | 44.8621 m  | 3.9031 m   | N/A  |
| CT2                                      | 5.3879 m   | 2.0052 m   | N/A  |
| CT3                                      | 345.5097 m | 33.4696 m  | N/A  |
| CT4                                      | 1.8077     | 11.0664 m  | N/A  |

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ ) |            |            |      |
|----------------------------------------------------|------------|------------|------|
| Junction to                                        | Ambient    | Case       | Foot |
| RF1                                                | 4.0515     | 792.5640 m | N/A  |
| RF2                                                | 9.4023     | 767.0347 m | N/A  |
| RF3                                                | 14.3801    | 927.8400 m | N/A  |
| RF4                                                | 37.1661    | 112.5613 m | N/A  |
| Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )  |            |            |      |
| Junction to                                        | Ambient    | Case       | Foot |
| CF1                                                | 7.9672 m   | 1.2344 m   | N/A  |
| CF2                                                | 47.7128 m  | 4.3773 m   | N/A  |
| CF3                                                | 344.9576 m | 6.4272 m   | N/A  |
| CF4                                                | 1.7342     | 61.0347 m  | N/A  |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

